

# SBD20100TCTB、SBDF20100TCTB

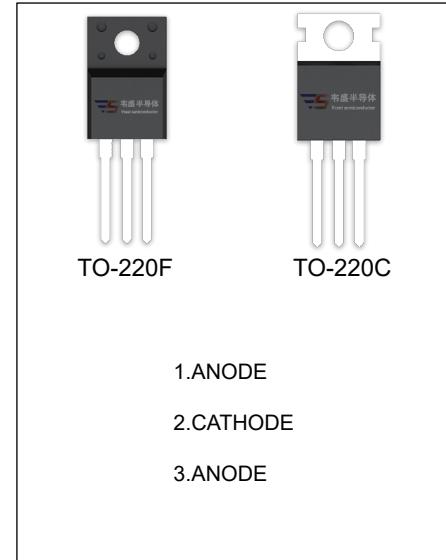
SCHOTTKY BARRIER RECTIFIER

## MAIN CHARACTERISTICS

$I_o$	20 (2×10) A
$V_{RRM}$	100 V
$T_j$	150 °C
$V_{F(ty)}$	0.62V (@ $T_j=125^\circ\text{C}$ )

## FEATURES

- Low Power Loss, High Efficiency
- Guard Ring Die Construction for Transient Protection
- High Current Capability and Low Forward Voltage Drop



## MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ unless otherwise noted )

Symbol	Parameter	SBD		Unit
		20100TCTB	F20100TCTB	
$V_{RRM}$	Peak repetitive reverse voltage			
$V_{RWM}$	Working peak reverse voltage		100	V
$V_R$	DC blocking voltage			
$V_{R(RMS)}$	RMS reverse voltage		70	V
$I_o$	Average rectified output current		20	A
$I_{FSM}$	Non-Repetitive peak forward surge current (8.3ms half sine wave)		150	A
$R_{\Theta JC}$	Thermal resistance from junction to case , $T_c=25^\circ\text{C}$	2.0	3.0	°C/W
$R_{\Theta JA}$	Thermal resistance from junction to ambient		62.5	°C/W
$T_j$	Junction temperature		150	°C
$T_{stg}$	Storage temperature		-55~+150	°C

## ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions		Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	$I_R=1\text{mA}$		100			V
Reverse current	$I_R$	$V_R=100\text{V}$	$T_j = 25^\circ\text{C}$		5.0	100	uA
			$T_j = 125^\circ\text{C}$		5.0		mA
Forward voltage	$V_F$	$I_F=5\text{A}$	$T_j = 25^\circ\text{C}$		0.54		V
			$T_j = 125^\circ\text{C}$		0.50		V
		$I_F=10\text{A}$	$T_j = 25^\circ\text{C}$		0.66	0.75	V
			$T_j = 125^\circ\text{C}$		0.62		V

\*Pulse test: pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2.0\%$ .

FIG.1: FORWARD CURRENT DERATING CURVE

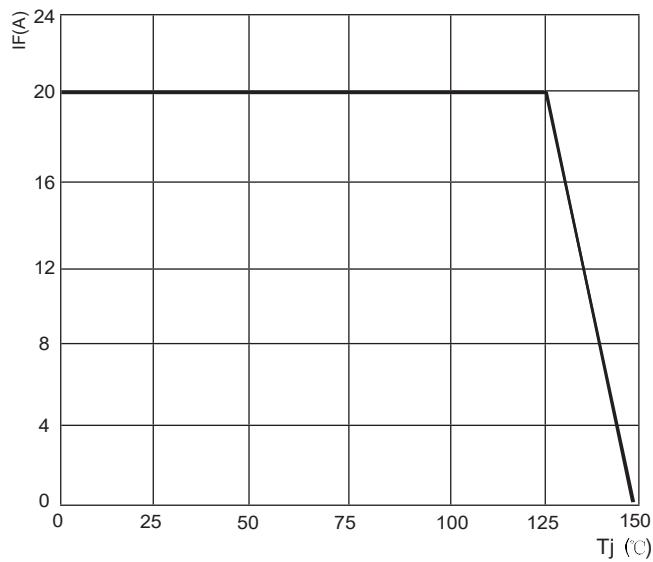


FIG.2: TYPICAL FORWARD CHARACTERISTICS

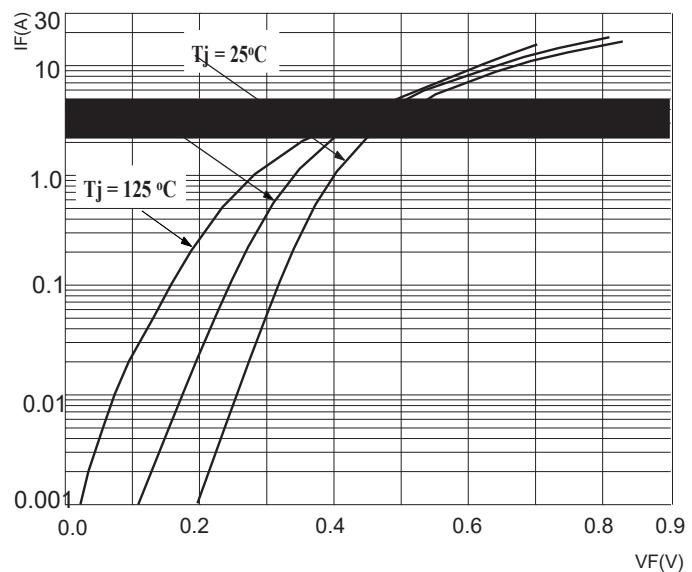


FIG.3: TOTAL CAPACITANCE DERATING CURVE

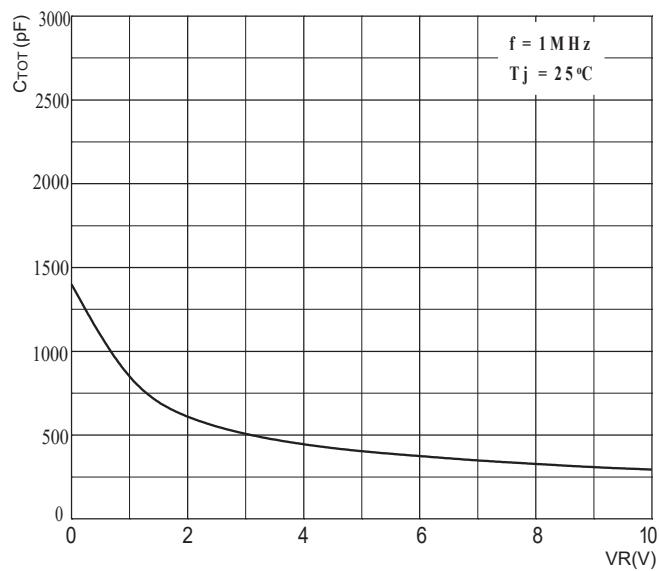


FIG.4: TYPICAL REVERSE CHARACTERISTICS

